

2SK3378

Silicon N Channel MOS FET High Speed Switching

REJ03G1599-0200

(Previous: ADE-208-805)

Rev.2.00 Oct 23, 2007

Features

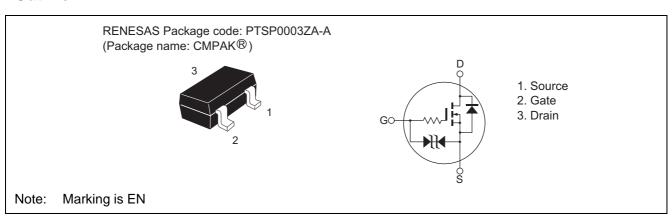
• Low on-resistance

$$R_{DS} = 2.7 \Omega \text{ typ. } (V_{GS} = 10 \text{ V}, I_D = 50 \text{ mA})$$

 $R_{DS} = 4.7 \Omega \text{ typ. } (V_{GS} = 4 \text{ V}, I_D = 20 \text{ mA})$

- 4 V gate drive device.
- Small package (CMPAK)

Outline



^{*}CMPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Rating

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	100	mA
Drain peak current	I _{D(pulse)} Note1	400	mA
Body-drain diode reverse drain current	I _{DR}	100	mA
Channel dissipation	Pch Note 2	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

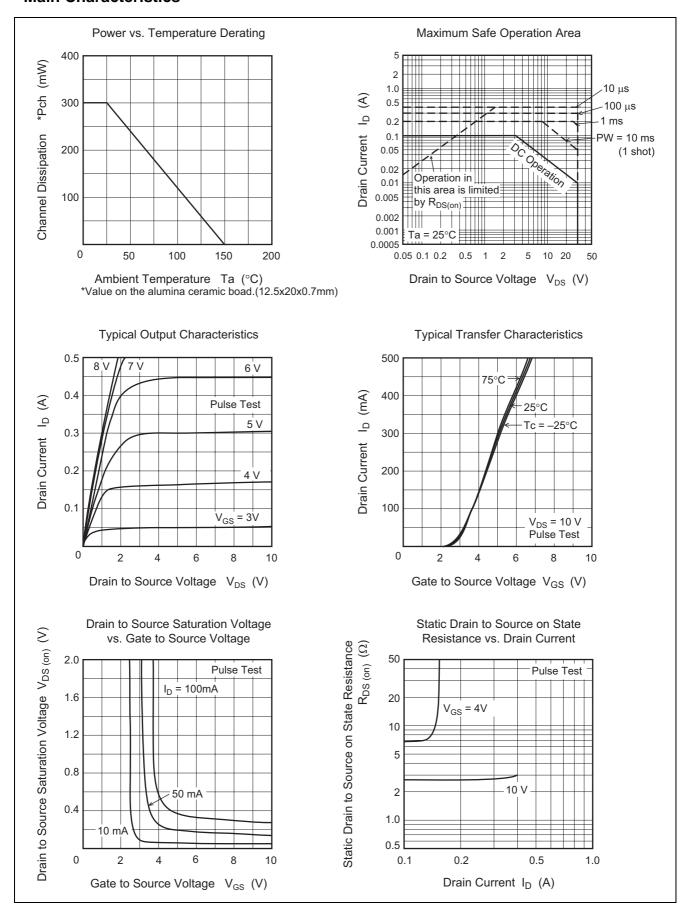
Electrical Characteristics

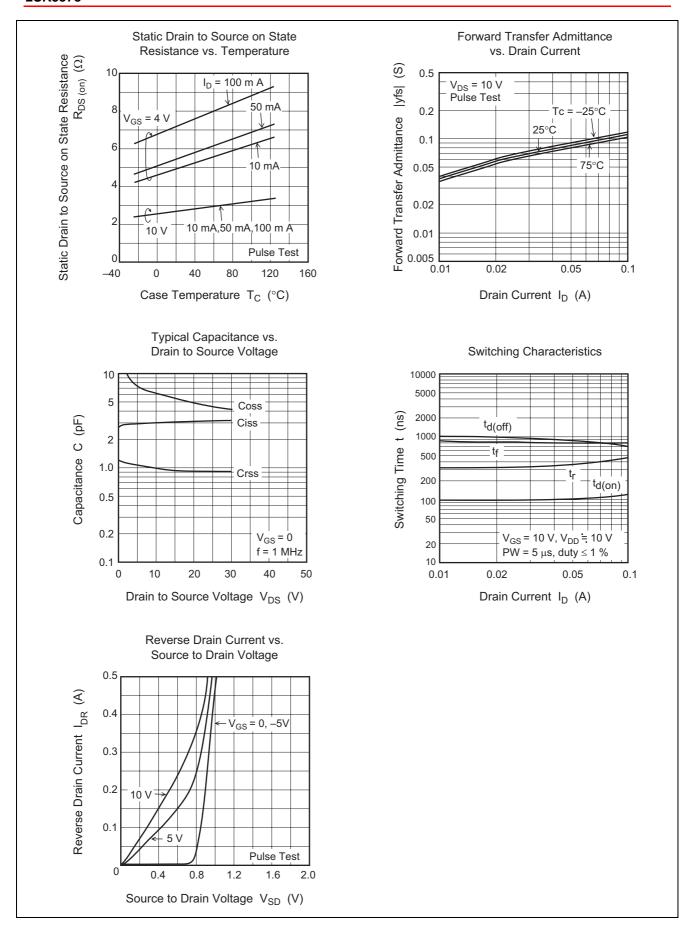
 $(Ta = 25^{\circ}C)$

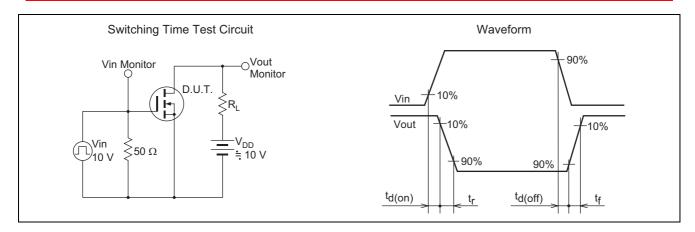
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 100 \mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±5	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.3	_	2.3	V	$I_D = 10 \mu A, V_{DS} = 5 V$
Static drain to source on state	R _{DS(on)}	_	2.7	3.5	Ω	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}^{\text{Note 3}}$
resistance	R _{DS(on)}	_	4.7	7.0	Ω	$I_D = 20 \text{ mA}, V_{GS} = 4 \text{ V}^{\text{Note 3}}$
Forward transfer admittance	y _{fs}	55	85	_	mS	$I_D = 50 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note 3}}$
Input capacitance	Ciss	_	3	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	8	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	1	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	100	_	ns	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$
Rise time	t _r	_	330	_	ns	$R_L = 200 \Omega$
Turn-off delay time	t _{d(off)}	_	1150	_	ns	
Fall time	t _f	_	940	_	ns	

Notes: 3. Pulse test

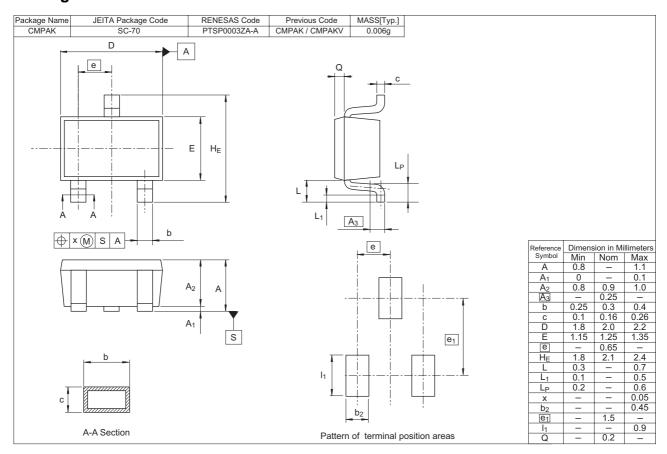
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
2SK3378ENTL-E	3000 pcs	Taping
2SK3378ENTR-E	3000 pcs	Taping

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